

Polar[™] Power MOSFET HiPerFET[™]

IXFH15N100P IXFV15N100PS

N-Channel Enhancement Mode Avalanche Rated Fast Intrinsic Diode

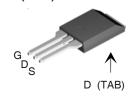


Symbol	Test Conditions	Maximum F	Ratings
V _{DSS}	$T_J = 25^{\circ}C$ to $150^{\circ}C$	1000	V
V _{DGR}	$T_{_{ m J}}$ = 25°C to 150°C, $R_{_{ m GS}}$ = 1M Ω	1000	V
V _{gss}	Continuous	± 30	V
V _{GSM}	Transient	± 40	V
I _{D25}	T _C = 25°C	15	Α
I _{DM}	$\rm T_{_{\rm C}}$ = 25°C, pulse width limited by $\rm T_{_{\rm JM}}$	40	Α
I _{AR}	T _c = 25°C	7.5	А
E _{AS}	$T_{c} = 25^{\circ}C$	500	mJ
dV/dt	$I_{S} \leq I_{DM}, V_{DD} \leq V_{DSS}, T_{J} \leq 150^{\circ}C$	15	V/ns
P _D	$T_{c} = 25^{\circ}C$	543	W
T _J		-55 +150	°C
$T_{_{ m JM}}$		150	°C
T_{stg}		-55 +150	°C
T _L	Maximum lead temperature for soldering	300	°C
T _{SOLD}	Plastic body for 10s	260	°C
M _d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
F _c	Mounting force (PLUS 220)	1165/2.514.6	N/lb.
Weight	TO-247 PLUS 220 types	6 4	g g

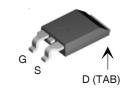
Symbol (Τ _J = 25°C, υ	Test Conditions unless otherwise specified)	Cha Min.	racteris Typ.		
BV _{DSS}	$V_{GS} = 0V, I_{D} = 1mA$	1000			V
$V_{\rm GS(th)}$	$V_{DS} = V_{GS}, I_D = 1 \text{mA}$	3.5		6.5	V
GSS	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	nA
I _{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_{J} = 125^{\circ}C$				μA mA
R _{DS(on)}	$V_{GS} = 10V, I_{D} = 0.5 \cdot I_{D2S}, \text{ Note 1}$		670	760	mΩ

 $V_{DSS} = 1000V$ $I_{D25} = 15A$ $R_{DS(on)} \le 760m\Omega$ $t \le 300ns$

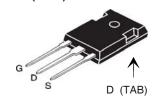
PLUS220 (IXFV)



PLUS220SMD (IXFV_S)



TO-247 (IXFH)



G = Gate D = DrainS = Source TAB = Drain

Features

- International standard packages
- Fast recovery diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

Applications:

- Switched-mode and resonant-mode power supplies
- DC-DC Converters
- Laser Drivers
- AC and DC motor controls
- Robotics and servo controls



IXFH15N100P IXFV15N100P IXFV15N100PS

Symbol	Test Conditions	Characteristic Values		
$(T_J = 25^\circ)$	C unless otherwise specified)	Min.	Тур.	Max.
g _{fs}	$V_{DS} = 20V, I_{D} = 0.5 \cdot I_{D25}, \text{ Note 1}$	6.5	10.5	S
C _{iss})		5140	pF
C _{oss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		322	pF
C _{rss}	J		43	pF
R_{gi}	Gate input resistance		1.20	Ω
t _{d(on)}	Resistive Switching Times		41	ns
t _r			44	ns
$\mathbf{t}_{d(off)}$	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25}$		44	ns
t _f	$\int R_{G} = 2\Omega \text{ (External)}$		58	ns
Q _{g(on)})		97	nC
\mathbf{Q}_{gs}	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25}$		38	nC
\mathbf{Q}_{gd}	J		42	nC
R _{thJC}				0.23 °C/W
R _{thCS}	(TO-247, PLUS220)		0.21	°C/W

Source-Drain Diode		Characteristic Values			
$T_{\rm J} = 25^{\circ}$	C unless otherwise specified)	Min.	Тур.	Max.	
I _s	$V_{GS} = 0V$			15	Α
I _{SM}	Repetitive			60	Α
V _{sD}	$I_F = I_S$, $V_{GS} = 0V$, Note 1			1.5	V
t _{rr}	I = 7.5A - di/dt = 100A/us			300	ns

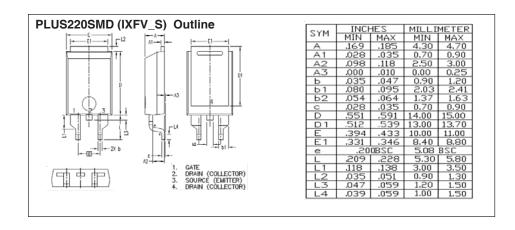
Note 1: Pulse test, $t \le 300\mu s$; duty cycle, $d \le 2\%$.

 $V_{R} = 100V, V_{GS} = 0V$

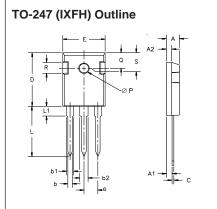
 \mathbf{Q}_{RM}

I_{RM}

 $I_{\rm F} = 7.5 A$, $-di/dt = 100 A/\mu s$



PLUS220 (IXFV) Outline DRAIN (COLLECTOR) SOURCE (EMITTER) DRAIN (COLLECTOR) MILLIMETER MIN MAX 4.30 4.70 0.70 0.90 2.50 1.30 MYZ MIN MAX Α .185 .169 Α2 .098 .118 .047 Ъ .080 ,095 064 b2 .054 .035 0.70 .591 14.00 .539 13.00 551 D 394 .433 10.00 331 346 .100BSC 8.40 8.80 2.54 BSC 551 138 051 13.00 14.00 3,00 0,90 .118 .059 1.20 .047



μС

Α

0.6

7

Millimeter		Inches	
Min.	Max.	Min.	Max.
4.7	5.3	.185	.209
2.2	2.54	.087	.102
2.2	2.6	.059	.098
1.0	1.4	.040	.055
1.65	2.13	.065	.084
2.87	3.12	.113	.123
.4	.8	.016	.031
20.80	21.46	.819	.845
15.75	16.26	.610	.640
5.20	5.72	0.205	0.225
19.81	20.32	.780	.800
	4.50		.177
3.55	3.65	.140	.144
5.89	6.40	0.232	0.252
4.32	5.49	.170	.216
6.15	BSC	242	BSC
	Min. 4.7 2.2 2.2 1.0 1.65 2.87 .4 20.80 15.75 5.20 19.81 3.55 5.89 4.32	Min. Max. 4.7 5.3 2.2 2.54 2.2 2.6 1.0 1.4 1.65 2.13 2.87 3.12 .4 .8 20.80 21.46 15.75 16.26 5.20 5.72 19.81 20.32 4.50 3.65 5.89 6.40 4.32 5.49	Min. Max. Min. 4.7 5.3 .185 2.2 2.54 .087 2.2 2.6 .059 1.0 1.4 .040 1.65 2.13 .065 2.87 3.12 .113 .4 .8 .016 20.80 21.46 .819 15.75 16.26 .610 5.20 5.72 0.205 19.81 20.32 .780 4.50 3.55 3.65 .140 5.89 6.40 0.232 4.32 5.49 .170

IXYS reserves the right to change limits, test conditions, and dimensions.



Fig. 1. Output Characteristics @ 25°C

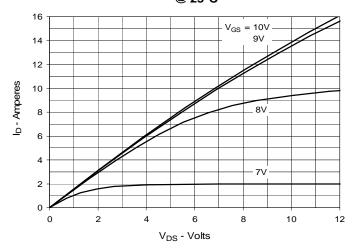


Fig. 2. Extended Output Characteristics @ 25°C

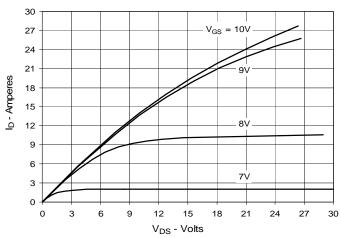


Fig. 3. Output Characteristics @ 125°C

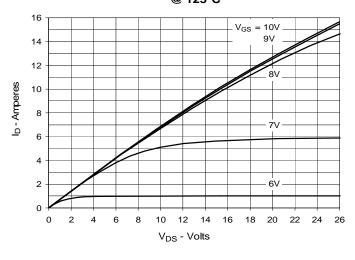


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 7.5A$ Value vs. Junction Temperature

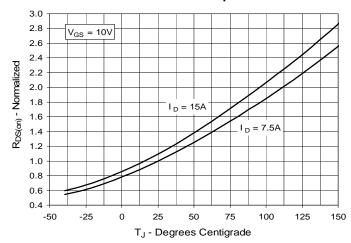


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 7.5A$ Value vs. Drain Current

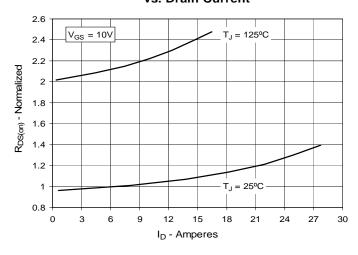


Fig. 6. Maximum Drain Current vs.

Case Temperature

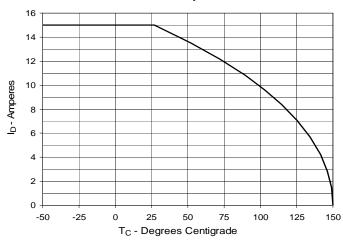




Fig. 7. Input Admittance

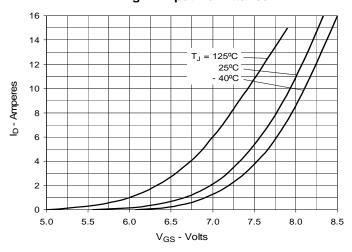


Fig. 8. Transconductance

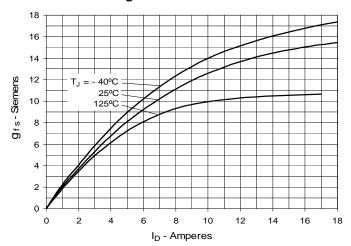


Fig. 9. Forward Voltage Drop of Intrinsic Diode

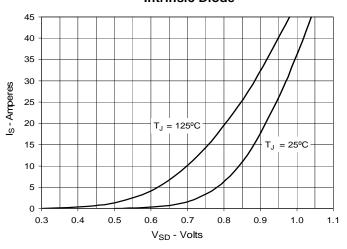


Fig. 10. Gate Charge

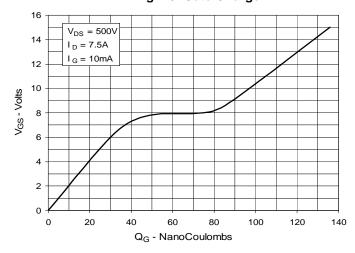


Fig. 11. Capacitance

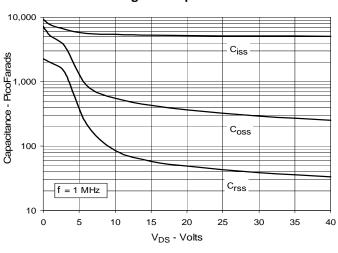
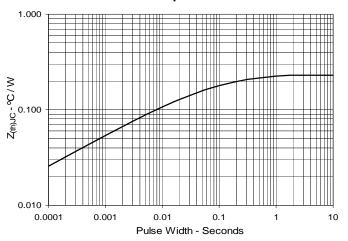


Fig. 12. Maximum Transient Thermal Impedance



IXYS reserves the right to change limits, test conditions, and dimensions.

